Construction and Characterization of (Y,Yb)MnO$_3$/HfO$_2$ Stacking Layers for Application to FeRAM

Kazuyuki Suzuki, Kaori Nishizawa, Takeshi Miki and Kazumi Kato
National Institute of Advanced Industrial Science and Technology (AIST)
2266-98 Anagahora, Shimoshidami, Moriyama-ku, Nagoya 463-8560, Japan
kz-suzuki@aist.go.jp
http://www.aist.go.jp/index_en.html

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Introduction
Recently, ferroelectric random access memories (FeRAM) have attracted much attention as a nonvolatile memory device. Particularly, field effect transistor (FET)-type memory has received great attention as next-generation memory because it has an advantage of high speed, low power consumption, reducing the memory cell size and nondestructive readout. RMnO$_3$ (R:Y, rare earth) with the hexagonal structure has been nominated for application of the FET-type nonvolatile memory because it has a low dielectric constant. In this paper, the (Y,Yb)MnO$_3$/HfO$_2$ stacking layer was constructed through the chemical solution process.

Experimental Procedure
HfO$_2$ insulating layers were prepared by spin coating Hf-based alkoxy-derived solutions. The as-deposited thin film was dried at 150°C and calcined at 350°C for 10 min in air. Then, the film was heated by rapid thermal annealing. For preparation of (Y,Yb)MnO$_3$ precursor solutions, yttrium iso-propoxide, ytterbium iso-propoxide and manganese iso-propoxide were selected as starting chemicals. (Y,Yb)MnO$_3$ films were prepared by spin coating the precursor solutions. The as-deposited films were dried at 150°C and calcined at 350°C for the 10min in air. Then, the films were heated by a rapid thermal annealing at 750°C in argon.

Results and Discussion
For down-sizing the structure, lowering the operating voltage and improvement of the electrical properties, the controls of the film thickness, interface structure, orientation and crystallinity of the both insulating and ferroelectric films were necessary. The degree of c-axis orientation and crystallinity of the Y$_{0.5}$Yb$_{0.5}$MnO$_3$ films were improved on the 10nm-thick HfO$_2$ film deposited by using the diluted Hf-based solution. The electrical properties were improved in the MFIS structure with 10nm-thick insulating layer and 200nm-thick ferroelectric film. The clockwise C-V hysteresis induced by ferroelectric polarization switching was observed in the MFIS structures. The memory window of the MFIS using the improved HfO$_2$ thin layer was about 2V and the retention time was over 10$^5$s. The results of the alkoxy-derived MFIS structure would work for development of FET-type FeRAM devices.
**Construction of MFIS Structure**

- metal
- ferroelectrics
- insulator
- HfO$_2$
- Si

**Properties of (Y,Yb)MnO$_3$/HfO$_2$/Si Structure**

![Graph showing polarization vs. electric field for (Y,Yb)MnO$_3$](image)

- $P$ vs. $E$
- Electric field (kV/cm)
- Polarization ($\mu$C/cm$^2$)

![Graph showing capacitance vs. applied voltage and time](image)

- Capacitance (pF)
- Applied voltage (V)
- Time (sec)

**Kazuyuki Suzuki**

Tailored Liquid Integration Group  
Advanced Manufacturing Research Institute  
National Institute of Advanced Industrial Science and Technology (AIST)  
2266-98 Anagahora, Shimoshidami, Moriyama-ku, Nagoya 463-8560, Japan  
Phone: +81 52-736-7236  
Fax: +81 52-736-7234  
e-mail: kz-suzuki@aist.go.jp

**Education:**

Ph.D., Graduate School of Engineering, Nagoya University, -3/2000  
Major: Applied chemistry  
Thesis: “Preparation and characterization of ferroelectric K(Ta,Nb)O$_3$ thin films”

**Work Experience:**

4/2000-present  
National Institute of Advanced Industrial Science and Technology (AIST)  
Subject: “Preparation of YMnO$_3$-based ferroelectric films for FeRAM application.”

**Field of Study**

Ferroelectrics, Thin film, Chemical solution process, etc.